

#### STL150N3LLH5

# N-channel 30 V, 0.0014 Ω typ., 35 A STripFET™ V Power MOSFET in a PowerFLAT™ 5x6 package

Datasheet - production data

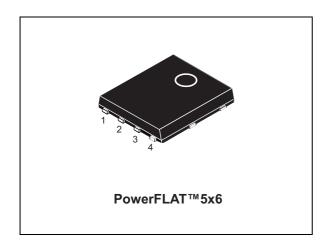
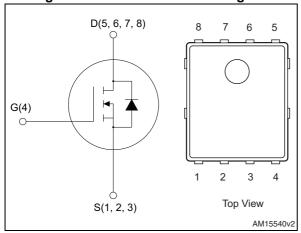


Figure 1. Internal schematic diagram



#### **Features**

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STL150N3LLH5	30 V	$0.00175\Omega$	35 A <sup>(1)</sup>

- 1. The value is rated according  $R_{thj\text{-pcb}}$
- R<sub>DS(on)</sub> \* Q<sub>g</sub> industry benchmark
- Extremely low on-resistance R<sub>DS(on)</sub>
- · High avalanche ruggedness
- Low gate drive power losses

#### **Applications**

· Switching applications

#### **Description**

This device is an N-channel Power MOSFET developed using STMicroelectronics' STripFET™V technology. The device has been optimized to achieve very low on-state resistance, contributing to a FOM that is among the best in its class.

**Table 1. Device summary** 

Order code	Marking	Packages	Packaging
STL150N3LLH5	150N3LH5	PowerFLAT™ 5X6	Tape and reel

Contents STL150N3LLH5

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STL150N3LLH5 Electrical ratings

# 1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source voltage	30	V
V <sub>GS</sub>	Gate-source voltage	± 22	V
I <sub>D</sub> <sup>(1)</sup>	Drain current (continuous) at T <sub>C</sub> = 25 °C	195	Α
I <sub>D</sub> <sup>(1)</sup>	Drain current (continuous) at T <sub>C</sub> = 100 °C	122	Α
I <sub>D</sub> <sup>(2)</sup>	Drain current (continuous) at T <sub>pcb</sub> = 25 °C	35	Α
I <sub>D</sub> <sup>(2)</sup>	Drain current (continuous) at T <sub>pcb</sub> =100 °C	21.8	Α
I <sub>DM</sub> <sup>(3)</sup>	Drain current (pulsed)	140	Α
P <sub>TOT</sub> (1)	Total dissipation at T <sub>C</sub> = 25 °C	114	W
P <sub>TOT</sub> (2)	Total dissipation at T <sub>pcb</sub> = 25 °C	4	W
T <sub>J</sub> T <sub>stg</sub>	Operating junction temperature Storage temperature	-55 to 150	°C

<sup>1.</sup> The value is rated according  $R_{thj-c}$ 

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case	1.1	°C/W
R <sub>thj-pcb</sub> (1)	Thermal resistance junction-pcb	31.3	°C/W

<sup>1.</sup> When mounted on FR-4 board of 1inch², 2oz Cu, t < 10 sec

Table 4. Avalanche data

Symbol	Parameter	Value	Unit
I <sub>AV</sub>	Not-repetitive avalanche current, (pulse width limited by T <sub>j max</sub> )	17	Α
E <sub>AS</sub>	Single pulse avalanche energy (starting $T_J = 25$ °C, $I_D = I_{AV}$ , $V_{DD} = 24$ V)	300	mJ

<sup>2.</sup> The value is rated according  $R_{\mbox{\scriptsize thj-pcb}}$ 

<sup>3.</sup> Pulse width limited by safe operating area

Electrical characteristics STL150N3LLH5

#### 2 Electrical characteristics

(T<sub>CASE</sub> = 25 °C unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	$I_D = 250 \ \mu A, \ V_{GS} = 0$	30			V
I <sub>DSS</sub>	Zero gate voltage drain	$V_{DS} = 30 \text{ V}$ $V_{GS} = 0$			1	μΑ
1055	current	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 T <sub>C</sub> =125 °C			10	μΑ
I <sub>GSS</sub>	Gate body leakage current	$V_{GS} = \pm 22 \text{ V}, V_{DS} = 0$			±100	nA
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1	1.55	2.2	٧
R <sub>DS(on)</sub>	Static drain-source on-	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 17.5 A		0.0014	0.00175	Ω
	resistance	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 17.5 A		0.0019	0.0024	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C <sub>iss</sub>	Input capacitance		-	5800	-	pF
C <sub>oss</sub>	Output capacitance	V <sub>DS</sub> = 25 V, f=1 MHz,	-	1147	-	pF
C <sub>rss</sub>	Reverse transfer capacitance	V <sub>GS</sub> =0	-	127	-	pF
$Q_g$	Total gate charge	V <sub>DD</sub> =15 V, I <sub>D</sub> = 35 A	-	40	-	nC
$Q_{gs}$	Gate-source charge	V <sub>GS</sub> =4.5 V (see Figure 14)	-	13.4	-	nC
$Q_{gd}$	Gate-drain charge		-	14.9	-	nC
R <sub>G</sub>	Gate input resistance	f = 1 MHz, gate DC Bias = 0, test signal level = 20 mV, $I_D = 0$	-	1.1	-	Ω

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t <sub>d(on)</sub>	Turn-on delay time		-	17.2	-	ns
t <sub>r</sub>	Rise time	$V_{DD}$ =15 V, $I_{D}$ = 17.5 A, $R_{G}$ =4.7 $\Omega$ , $V_{GS}$ =10 V (see Figure 13)	-	30.8	-	ns
t <sub>d(off)</sub>	Turn-off delay time		-	65.8	-	ns
t <sub>f</sub>	Fall time	,	-	47.8	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>SD</sub>	Source-drain current		ı		35	Α
I <sub>SDM</sub> <sup>(1)</sup>	Source-drain current (pulsed)		-		140	Α
V <sub>SD</sub> <sup>(2)</sup>	Forward on voltage	$I_{SD} = 35 \text{ A}, V_{GS} = 0$	-		1.1	V
t <sub>rr</sub>	Reverse recovery time	I <sub>SD</sub> = 35 A,	-	43.8		ns
Q <sub>rr</sub>	Reverse recovery charge	di/dt = 100 A/µs,	-	46		nC
I <sub>RRM</sub>	Reverse recovery current	V <sub>DD</sub> = 25 V	-	2.1		Α

<sup>1.</sup> Pulse width limited by safe operating area

<sup>2.</sup> Pulsed: pulse duration=300µs, duty cycle 1.5%

Electrical characteristics STL150N3LLH5

#### 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Thermal impedance

Figure 4. Output characteristics

Figure 5. Transfer characteristics

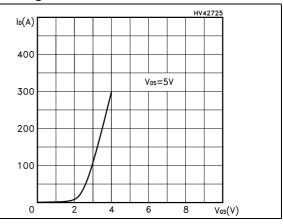


Figure 6. Normalized  $B_{VDSS}$  vs temperature

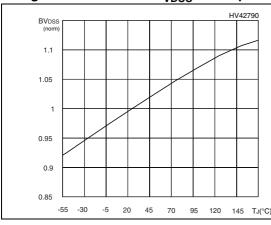
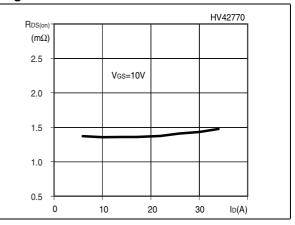


Figure 7. Static drain-source on-resistance



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Figure 8. Gate charge vs gate-source voltage

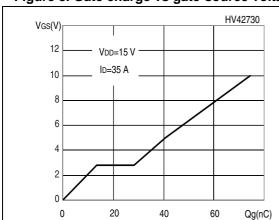
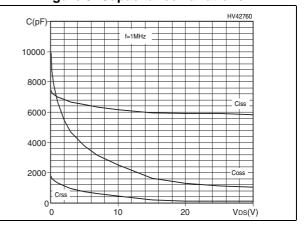


Figure 9. Capacitance variations



temperature

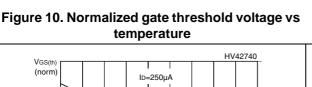


Figure 11. Normalized on-resistance vs temperature

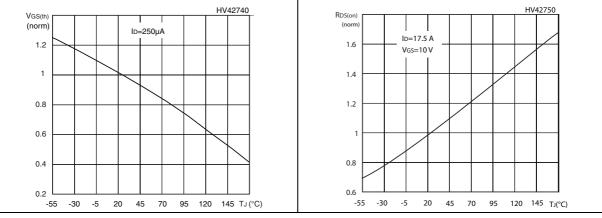
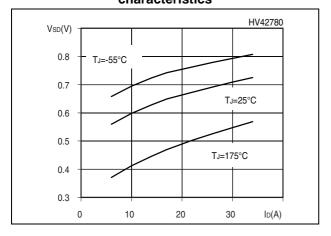


Figure 12. Source-drain diode forward characteristics



Test circuits STL150N3LLH5

#### 3 Test circuits

Figure 13. Switching times test circuit for resistive load

Figure 14. Gate charge test circuit

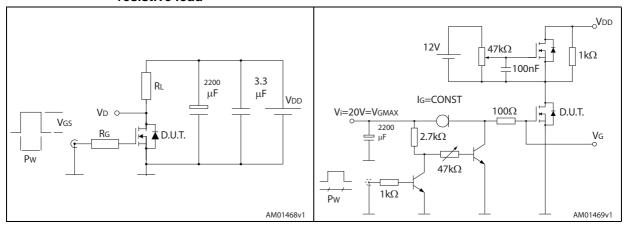


Figure 15. Test circuit for inductive load switching and diode recovery times

Figure 16. Unclamped inductive load test circuit

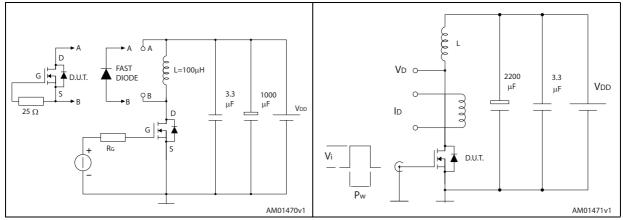
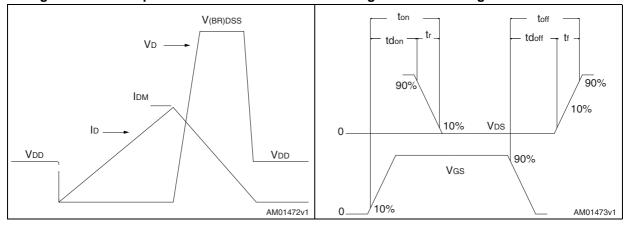


Figure 17. Unclamped inductive waveform

Figure 18. Switching time waveform



## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.



Table 9. PowerFLAT™ 5x6 type S-C mechanical data

Dim.		mm	
Dilli.	Min.	Тур.	Max.
Α	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
D		5.20	
E		6.15	
D2	4.11		4.31
E2	3.50		3.70
е		1.27	
e1		0.65	
L	0.715		1.015
K	1.05		1.35

Bottom view D'2 Pin 1 identification Side view  $\forall$ D Pin 1 Top view identification 8231817\_F\_C

Figure 19. PowerFLAT™ 5x6 type S-C mechanical data

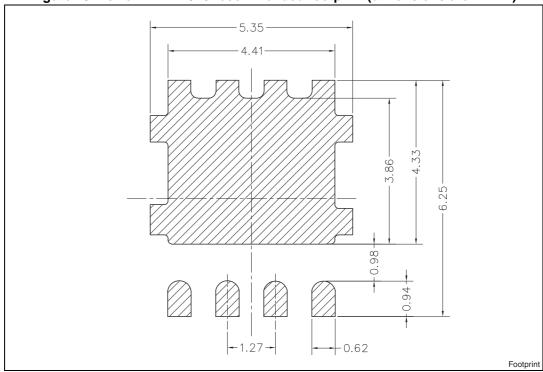


Figure 20. PowerFLAT™ 5x6 recommended footprint (dimensions are in mm)



STL150N3LLH5 Revision history

# 5 Revision history

**Table 10. Document revision history** 

Date	Revision	Changes
22-Oct-2007	1	First release
01-Apr-2008	2	Document status promoted from preliminary data to datasheet
23-Sep-2008	3	V <sub>GS</sub> value has been changed on <i>Table 2</i> and <i>Table 5</i>
12-Jun-2009	4	V <sub>GS(th)</sub> value has been changed on <i>Table 5</i>
05-Oct-2011	5	Section 4: Package mechanical data has been updated. Minor text changes.
30-Aug-2013	6	<ul> <li>Modified: Figure 1 and marking in Table 1</li> <li>Modified: I<sub>D</sub> value in Figure 11</li> <li>Updated: Figure 13, 14, 15 and 16</li> <li>Updated: Section 4: Package mechanical data</li> </ul>

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